

**Learning Objective: PN Junction Diode Physics**

**Problem 1.** A Silicon ( $n_i = 1.5 \times 10^{-10} \text{ cm}^{-3}$ ) PN junction diode is designed to operate at  $T = 300 \text{ K}$  such that the diode current is 10 mA at a forward bias diode voltage of 0.65 V. The current density is 20 A/cm<sup>2</sup> under this operating condition.

- (a) Suppose  $N_D = 5 \times 10^{17} \text{ cm}^{-3}$ ,  $N_A = 5 \times 10^{15} \text{ cm}^{-3}$ , calculate the **build-in potential barrier** of the PN junction diode.

$$\begin{aligned} V_{bi} &= \frac{kT}{q} \ln \left( \frac{N_D N_A}{n_i^2} \right) \\ &= (0.026) \ln \left[ \frac{(5 \times 10^{17})(5 \times 10^{15})}{(1.5 \times 10^{10})^2} \right] \\ &= 0.781 \text{ V} \end{aligned}$$

- (b) Calculate the **power consumption** of this PN junction diode.

$$P_D = V_D I_D = (0.65)(10) = 6.5 \text{ mW}$$

- (c) Determine the **cross sectional area** of this diode.

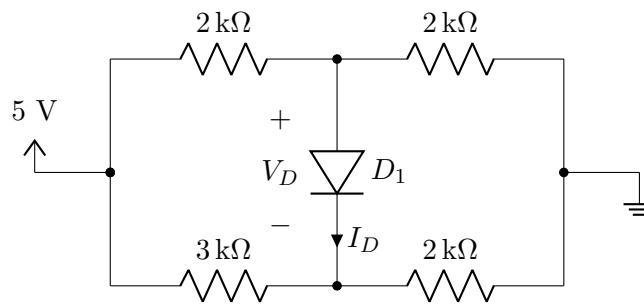
$$A = \frac{I_D}{J_D} = \frac{10 \times 10^{-3}}{20} = 5 \times 10^{-4} \text{ cm}^2$$

- (d) Determine the **reverse saturation current density** of this diode.

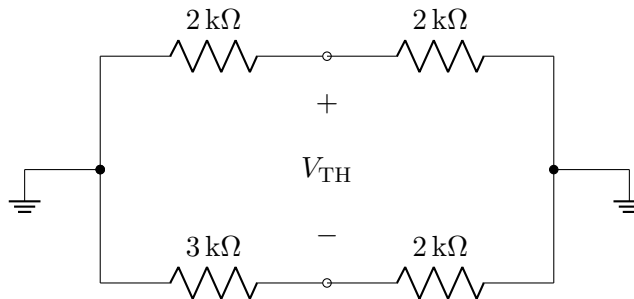
$$\begin{aligned} J_D &= J_S \left[ \exp \left( \frac{V_D q}{kT} \right) - 1 \right] \cong J_S \exp \left( \frac{V_D q}{kT} \right) \\ 20 &= J_S \exp \left( \frac{0.65}{0.026} \right) \\ J_S &= 2.78 \times 10^{-10} \frac{\text{A}}{\text{cm}^2} \end{aligned}$$

**Learning Objective: PN Junction Diode DC Analysis**

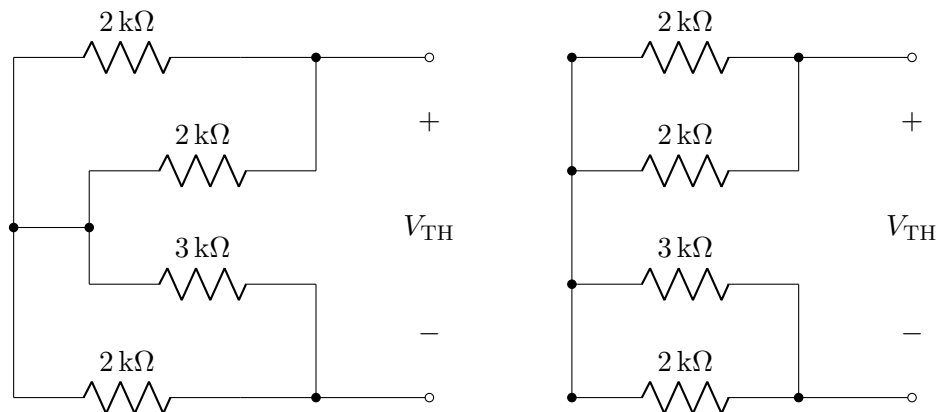
**Problem 2.** Calculate the **diode current** and **diode reverse saturation current** at  $T = 300$  K from the circuit shown below, under diode voltage of (a)  $V_D = 0.6$  V, (b)  $V_D = 0.7$  V.

**Solution:**

Separate the load (diode) from the circuit, then apply Thevenin Theorem to reduce the circuit. The voltage source in this circuit is independent, so Thevenin resistance  $R_{TH}$  can be calculated by finding the equivalent resistance from  $V_{TH}$  port with voltage source shorted:



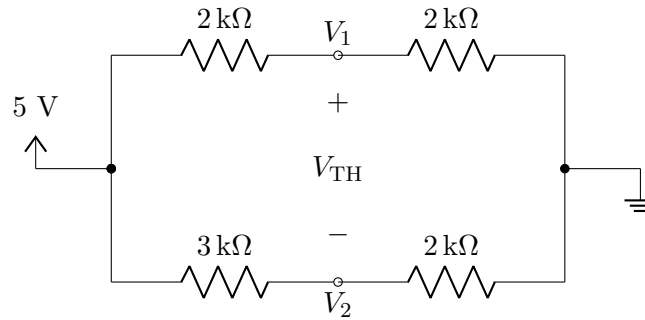
Remap this circuit by folding two  $2\text{ k}\Omega$  resistors on the right-hand side to the left, getting the following circuit:



Therefore:

$$\begin{aligned}
 R_{TH} &= 2\text{ k}\Omega // 2\text{ k}\Omega + 2\text{ k}\Omega // 3\text{ k}\Omega \\
 &= \boxed{2.2\text{ k}\Omega}
 \end{aligned}$$

Next, use node analysis to help find  $V_{TH}$ . I named the plus and minus port of  $V_{TH}$  as  $V_1$  and  $V_2$ :



The node voltages  $V_1$  and  $V_2$  can be found using voltage divider:

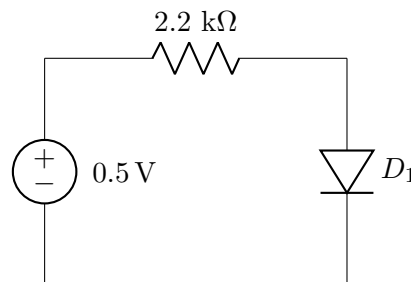
$$V_1 = 5 \times \frac{2 \times 10^3}{2 \times 10^3 + 2 \times 10^3} = 2.5 \text{ V}$$

$$V_2 = 5 \times \frac{2 \times 10^3}{3 \times 10^3 + 2 \times 10^3} = 2 \text{ V}$$

The Thevenin voltage  $V_{TH}$  can be expressed as

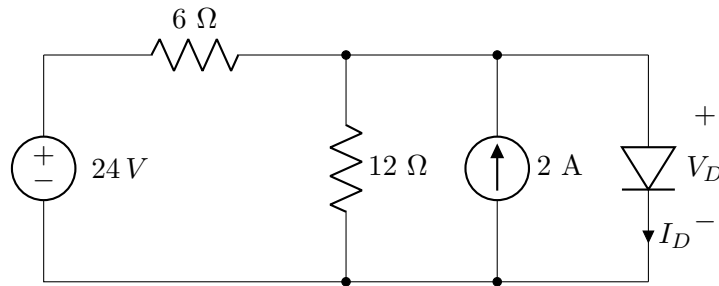
$$V_{TH} = V_1 - V_2 = \boxed{0.5 \text{ V}}$$

We get the following Thevenin equivalent circuit:



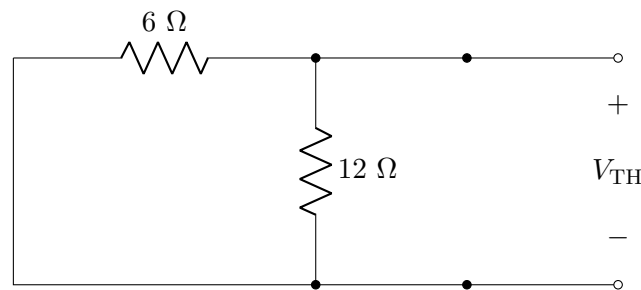
Because the Thevenin voltage is lower than the diode turn on voltage for both part (a)  $V_D = 0.6 \text{ V}$  and (b)  $V_D = 0.7 \text{ V}$ , the diode current for both case is  $\boxed{I_D = 0 \text{ A}}$ , and reverse saturation current  $\boxed{\text{can't determined}}$ .

**Problem 3.** Calculate the **diode current  $I_D$**  and **diode voltage  $V_D$**  at  $T = 300$  K from the circuit shown below. Assume the diode  $D_1$  is ideal. (Use  $I_s = 10^{-12}$  A)



**Solution:**

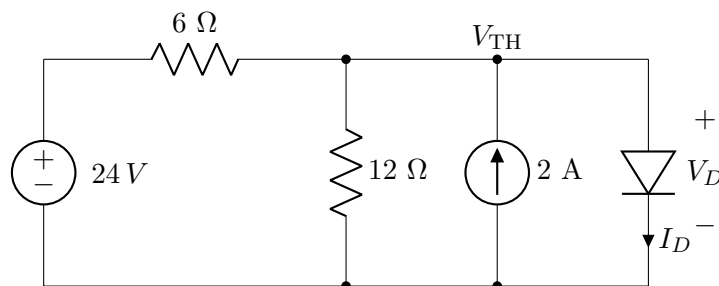
Separate the load (diode) from the circuit, then apply Thevenin Theorem to reduce the circuit. The voltage source and current source in this circuit are independent, so Thevenin resistance  $R_{TH}$  can be calculated by finding the equivalent resistance from  $V_{TH}$  port with voltage source shorted and current source removed:



Therefore:

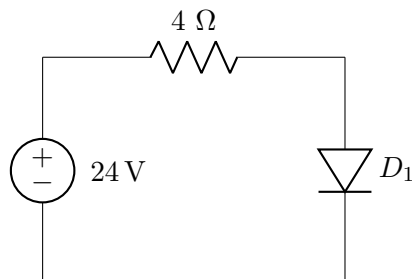
$$R_{TH} = 6\Omega // 12\Omega = \boxed{4\Omega}$$

Then mark the node between 6  $\Omega$  and 4  $\Omega$  resistor  $V_{TH}$ , and perform KCL:



$$\begin{aligned} \frac{V_{TH} - 24}{6} + \frac{V_{TH}}{12} &= 2 \\ 2(V_{TH} - 24) + V_{TH} &= 24 \\ V_{TH} &= \boxed{24\text{ V}} \end{aligned}$$

We get the following Thevenin equivalent circuit:



Applying both KVL and diode current equation to solve for  $V_D$  and  $I_D$ :

$$I_D = \frac{24 - V_D}{4}$$
$$I_D = \times 10^{-12} \exp\left(\frac{V_D}{0.026}\right)$$

By solving the system of equation get:  $V_D = 0.764 \text{ V}$ ,  $I_D = 5.809 \text{ A}$ .